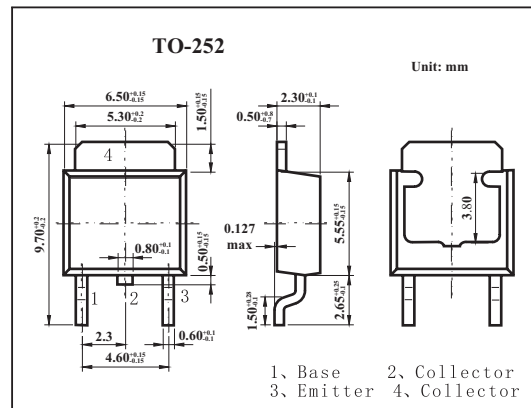


PNP Silicon Epitaxial Transistor

2SA1385-Z

■ Features

- Low $V_{CE(sat)}$: $V_{CE(sat)} = -0.18V$ Typ.
- Complement to 2SC3518-Z

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-60	V
Emitter-base voltage	V_{EBO}	-7	V
Collector Current (DC)	I_C	-5	A
Collector Current (Pulse) *	I_C	-7	A
Total Power Dissipation ($T_c = 25^\circ C$)	P_T	10	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* $PW \leq 10ms$, Duty Cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB} = -50V$, $I_E = 0$			-10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -7.0V$, $I_C = 0$			-10	μA
DC Current Gain	h_{FE1} *	$V_{CE} = -1.0V$, $I_C = -2.0A$	100	200	400	
DC Current Gain	h_{FE2} *	$V_{CE} = -1.0V$, $I_C = -5.0A$	50	100		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$ *	$I_C = -2.0A$, $I_B = -0.2A$		-0.18	-0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$ *	$I_C = -2.0A$, $I_B = -0.2A$			-1.2	V
Current Gain Bandwidth Product	f_T	$V_{CE} = -10V$, $I_C = -0.5A$		140		MHz
Turn-on Time	t_{on}	$V_{CC} = -10V$, $I_C = -2.0A$ $R_L = 50\Omega$ $I_{B1} = -I_{B2} = -0.2A$		0.08	1.0	μs
Storage Time	t_{stg}			0.55	2.5	
Fall Time	t_f			0.18	1.0	

* Pulsed: $PW \leq 350\mu s$, Duty Cycle $\leq 2\%$

■ hFE Classification

Marking	M	L	K
h_{FE1}	100 ~ 200	160 ~ 320	200 ~ 400